

High-Sensitivity Silicon Phototransistors

Optoelectronic Products

FPT120/A/B/C FPT130/A/B

General Description

The FPT120/A/B/C and FPT130/A/B are silicon nitride protected npn Planar phototransistors with exceptionally stable characteristics and high illumination-sensitivity. The case is made of a special plastic compound with transparent resin encapsulation. The controlled sensitivities offered in the A, B and C versions give the circuit designer increased flexibility.

High Illumination Sensitivity

Availability Of Base Pins For Flexible Circuit Design

Absolute Maximum Ratings

Maximum Temperature and Humidity

Storage Temperature	-55°C to +100°C
Operating Temperature	-55°C to +85°C
Pin Temperature (Soldering, 5 s)	260°C
Relative Humidity at 65°C	85%

Maximum Power Dissipation (Note 1)

Total Dissipation at $T_C = 25^\circ\text{C}$	200 mW
Derate Linearly from 25°C	3.33 mW/°C
Total Dissipation at $T_A = 25^\circ\text{C}$	100 mW
Derate Linearly from 25°C	1.67 mW/°C

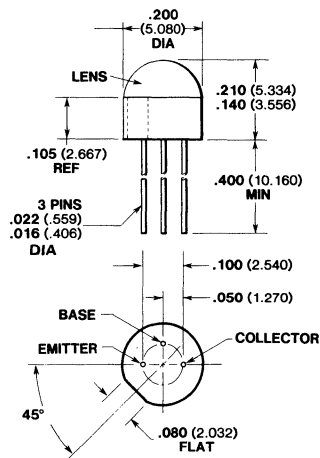
Maximum Voltage and Currents

$V_{CE(sus)}$	Collector-to-Emitter Sustaining Voltage (Note 4)	20 V
I_C	Collector Current	25 mA

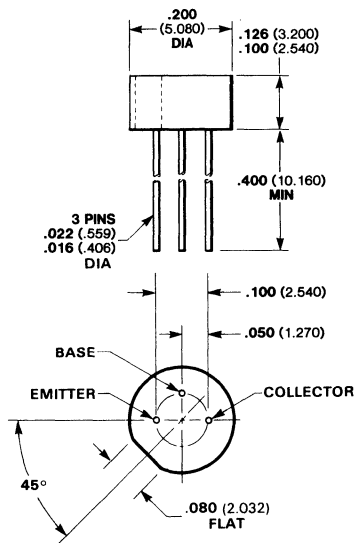
Package Outlines

FPT120/A/B/C

PHYSICAL DIMENSIONS



FPT130/A/B



Notes

All dimensions in inches **bold** and millimeters (parentheses)
Tolerance unless specified = $\pm .015$ ($\pm .381$)

Typical Electrical Characteristics

FPT120/A/B/C FPT130/A/B

Electrical Characteristics $T_A = 25^\circ\text{C}$

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
$V_{CEO(sus)}$	Collector-to-Emitter Sustaining Voltage (Note 4)	20	50		V	$I_C = 1\text{ mA}$ (Pulsed)
BV_{ECO}	Emitter-to-Collector Breakdown Voltage (Note 4)		5.0		V	$I_{EC} = 100\text{ }\mu\text{A}$
$V_{CE(sat)}$	Collector-to-Emitter Saturation Voltage, Tungsten Source (Note 2)		0.25	0.55	V	$I_C = 1\text{ mA}$, $H = 20\text{ mW/cm}^2$
I_{CEO}	Collector Dark Current (Note 4)		10	100	nA	$V_{CE} = 5.0\text{ V}$
$I_{CE(It)}$	Photo Current, Tungsten Source (Note 2)				mA	$V_{CE} = 5.0\text{ V}$, $H = 5\text{ mW/cm}^2$
	FPT120	2.0	7.5			
	FPT120A (Note 6)	7.5		22.5		
	FPT120B (Note 6)	10		20		
	FPT120C (Note 6)	16		25		
	FPT130	2.0	4.5			
	FPT130A (Note 7)	4.5		13.5		
	FPT130B (Note 7)	6.0		12		
$I_{CE(It)}$	Photo Current, GaAs Source (Note 3)				mA	$V_{CE} = 5.0\text{ V}$, $H = 1\text{ mW/cm}^2$
	FPT120	0.7	4.5			
	FPT130	0.7	2.7			
t_r	Light Current Rise Time (Note 5)		18		μs	
t_f	Light Current Fall Time (Note 5)		18		μs	

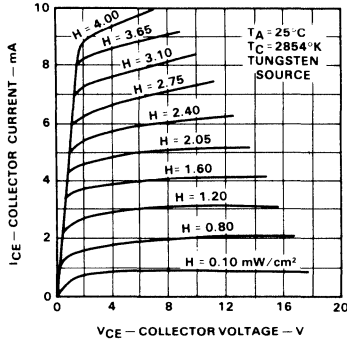
Notes

- These are steady-state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- Measured at noted irradiance as emitted from a tungsten filament lamp at a color temperature of 2854°K . The effective photosensitive area is typically 1.25 mm^2 (FPT120A/B) and 0.78 mm^2 (FPT130A/B).
- These are values obtained at noted irradiance as emitted from a GaAs source at 900 nm .
- Measured with radiation flux intensity of less than $0.1\text{ }\mu\text{W/cm}^2$ over the spectrum from $100\text{--}1500\text{ nm}$.
- Rise time is defined as the time required for I_{CE} to rise from 10% to 90% of peak value. Fall time is defined as the time required for I_{CE} to decrease from 90% to 10% of peak value. Test conditions are: $V_{CE} = 5.0\text{ V}$, $I_{CC} = 4.0\text{ mA}$, $R_L = 100\text{ }\Omega$, GaAs source.
- Same electrical characteristics as FPT120 except for $I_{CE(It)}$.
- Same electrical characteristics as FPT130 except for $I_{CE(It)}$.

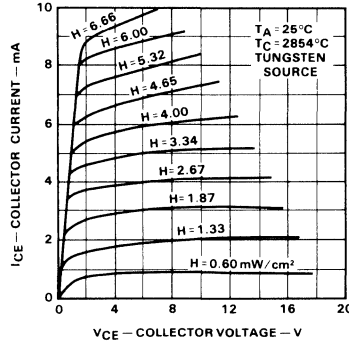
Typical Electrical Characteristic Curves

FPT120/A/B/C FPT130/A/B

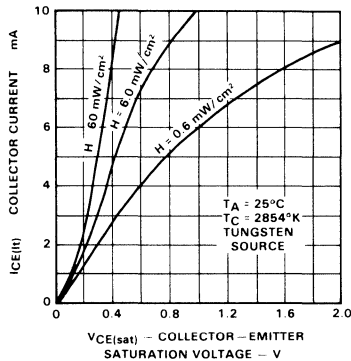
**FPT120/A/B/C Collector Current vs
Collector Voltage**



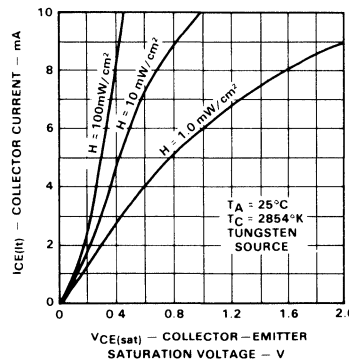
**FPT130/A/B/C Collector Current vs
Collector Voltage**



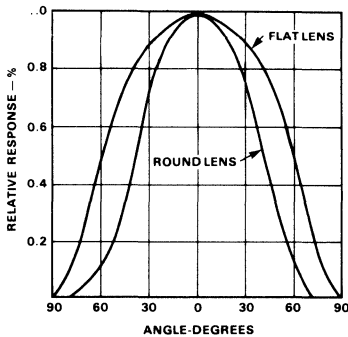
**Collector-Emitter Saturation
Voltage vs Collector Current**



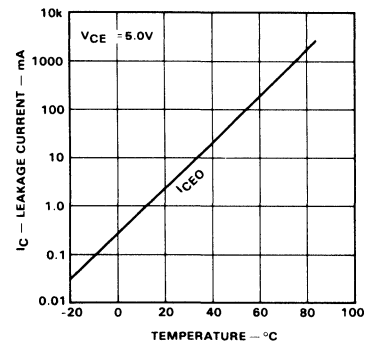
**Collector-Emitter Saturation
Voltage vs Collector Current**



Angular Response



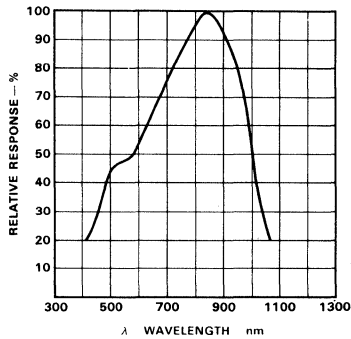
Collector Dark Current vs Temperature



Typical Electrical Characteristic Curves (Cont'd)

FPT120/A/B/C
FPT130/A/B

Relative Spectral Response



Rise And Fall Time vs Collector Current

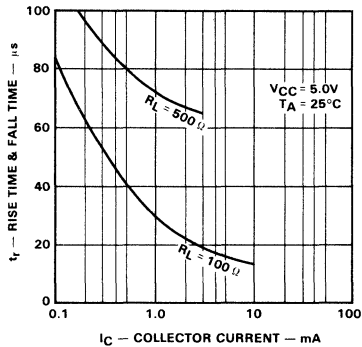
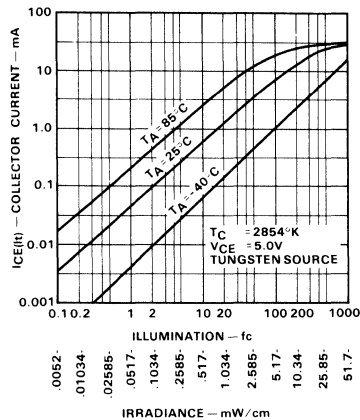


Photo Current Characteristics



Switching Time Measurement Circuit

